Please amend the claims as follows:

1. (Currently Amended) A semiconductor fabrication ~~system~~ apparatus to process a wafer, comprising:

an air-tight housing in which an inert gas is admittable and exhaustible; and

a plurality of adjacent deposition chambers positioned within the ~~system~~ air-tight housing.

2. (Currently Amended) The ~~system~~ apparatus of claim 1, wherein one of the deposition chambers is a facing target sputtering chamber.

3. (Currently Amended) The ~~system~~ apparatus of claim 2, wherein the deposition chamber further comprises:

a pair of target plates placed at opposite ends of said ~~air-tight~~ chamber respectively so as to face each other and form a plasma region therebetween;

a pair of magnets respectively disposed adjacent to said target plates such that magnet poles of different polarities face each other across said plasma region thereby to establish a magnetic field of said plasma region between said target plates;

a substrate holder disposed adjacent to said plasma region, said substrate holder adapted to hold a substrate on which an alloyed thin film is to be deposited; and

a back-bias power supply coupled to the substrate holder.

4. (Currently Amended) ~~A facing targets sputtering device according to~~ The apparatus of claim 3, wherein the back-bias power supply is a DC or an AC electric power source.

5. (Currently Amended) ~~A facing targets sputtering device according to~~ The apparatus of claim 1, further comprising a robot arm to move the wafer.

6. (Currently Amended) ~~A facing targets sputtering device according to~~ The apparatus of claim 1, further comprising a magnetron coupled to the chamber.

7. (Currently Amended) ~~A facing targets sputtering device according to~~ The apparatus of claim 1, further comprising a chuck heater mounted above the wafer.

8. (Currently Amended) The apparatus of claim 1, further comprising a rotary chuck to move a wafer.

9. (Currently Amended) The apparatus of claim 1, further comprising a linear motor to move the rotary chuck and sequentially expose the wafer to a plurality of chambers.

10. (Currently Amended) The apparatus of claim 1, wherein each chamber provides a collimated deposition pattern.

11. (Currently Amended) The apparatus of claim 1, wherein each chamber further comprises a door that opens during each chamber's deposition and closes when the chamber is not depositing.

12. (Currently Amended) The apparatus of claim 11, wherein each door comprises a baffle to catch falling particulates.

13. (Currently Amended) The apparatus of claim 1, wherein the chambers share magnets.

14. (Currently Amended) The apparatus of claim 1, further comprising a housing pump to evacuate air from the housing.

15. (Currently Amended) The apparatus of claim 1, wherein each chamber further comprises a chamber pump.

16. (Currently Amended) The apparatus of claim 1, further comprising a chuck supported from underneath rather than from the side.

17. (Currently Amended) The apparatus of claim 1, further comprising a jointed pendulum to support the wafer and keep the wafer at a constant vertical distance from ~~the~~ a target plate as the pendulum swings.

18. (Currently Amended) A method for sputtering a thin film onto a substrate, comprising:

providing a plurality of adjacent deposition chambers, each sharing at least a magnet with a neighboring chamber and having at least one target and a substrate having a film-forming surface portion and a back portion;

creating a magnetic field so that the film-forming surface portion is placed in the magnetic field with the magnetic field induced normal to the ~~substrate~~ film-forming surface portion

back-biasing the back portion of the substrate; and

sputtering material onto the film-forming surface portion.

19. (Currently Amended) A method as in claim 18, further comprising swinging the ~~wafer~~ substrate using a pendulum.

20. (Currently Amended) A method as in claim 18, further comprising supporting a chuck from underneath rather than side-way.